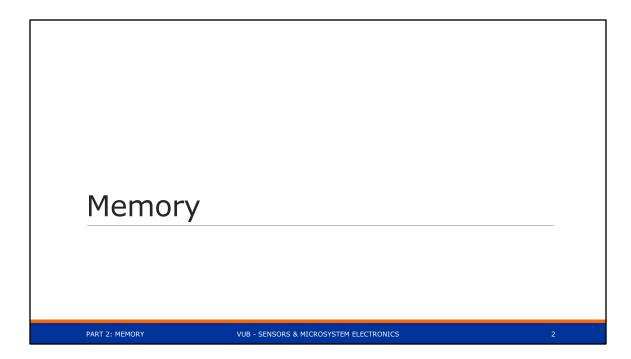


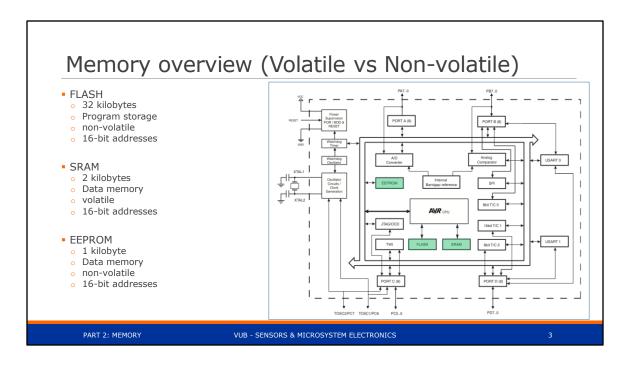




Sensors & Microsystem Electronics: microcontrollers

PART 2: MEMORY, TIMERS & INTERRUPTS





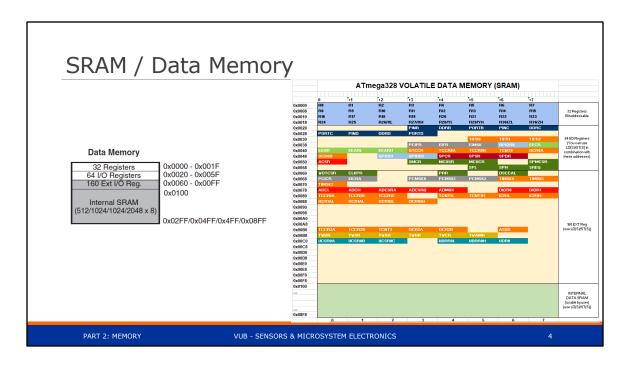
The microcontroller has three different memories: FLASH, SRAM and EEPROM.

Both FLASH and EEPROM are non-volatile, meaning they keep their content between power cycles. This is not the case with the SRAM which is volatile.

The flash memory is also called the program memory. This is because your compiled program is written here, and loaded when the microcontroller is running. It is not possible to write to this memory from your running program. Writing can only be done by the programmer. As a programmer you can store blocks of readonly data here to be read by your program.

The SRAM is your "working memory" this part of the memory can be used to temporarily store values. The SRAM has very fast access times and has a virtually unlimited number of read/write cycles.

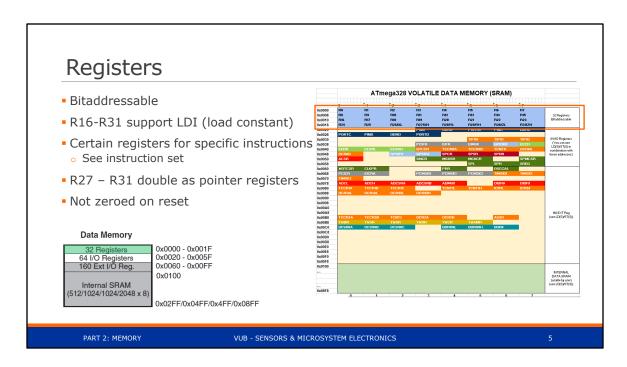
The EEPROM can be written from your code as opposed to the FLASH. It is used to store values that need to be kept between power cycles. Some examples of this are: settings, highscores, ... The EEPROM has slower access times, as well as a limited number of write-cycles (10k-100k)



The 32 registers on which one can do operations.

64 I/O registers. And 160 extended I/O registers. These registers are used to configure the peripherals of the microcontroller.

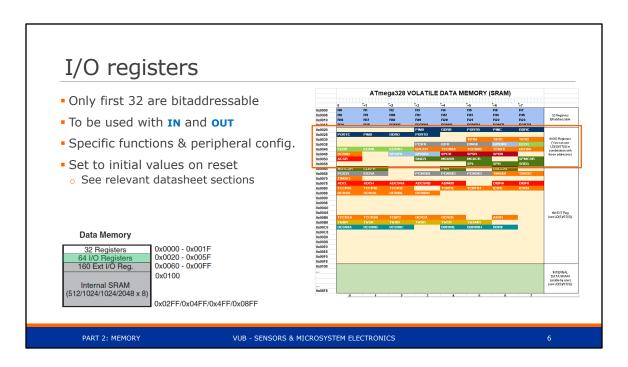
The internal SRAM: this is free memory space to be freely used by the programmer



The 32 registers on which one can do operations.

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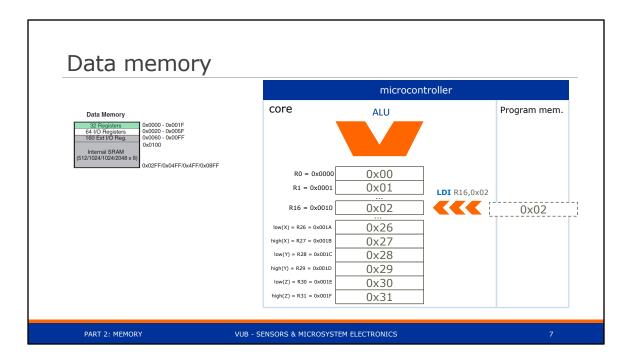
The internal SRAM: this is free memory space to be freely used by the programmer



The 32 registers on which one can do operations.

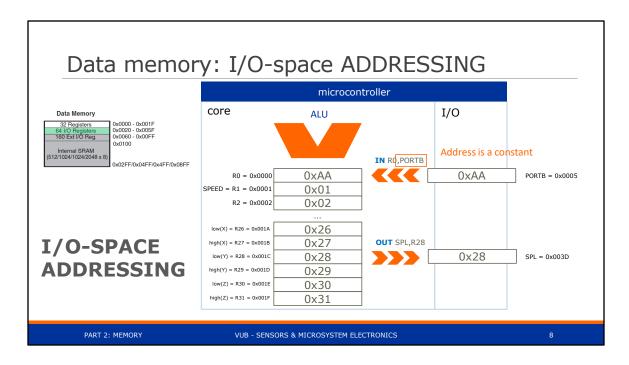
64 I/O registers. And 160 extended I/O registers. These registers are used to configure the peripherals of the microcontroller.

The internal SRAM: this is free memory space to be freely used by the programmer



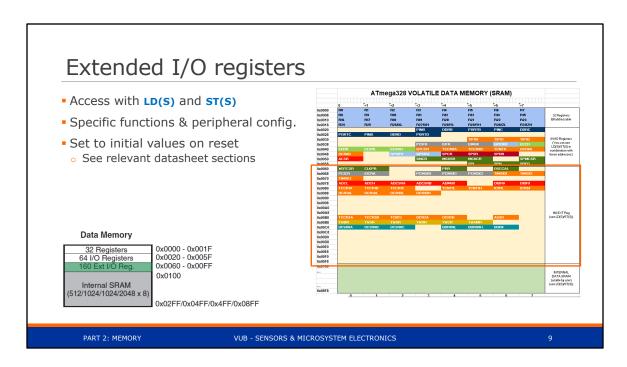
Only the first 32 registers are usable with instructions. Furthermore there can be some limitations on the instructions, e.g. Multiply stores the result in specific registers. As well as registers with additional functions such as the addressing registers.

The LDI instruction can load a constant in a registers. Like LDI R16,0x02 loads 0x02 in register 16. Note: the LDI instruction can only be used on R16-R31. To load a constant in any of the registers below 16, one needs to free up a register in the upper half, load it there with LDI, then copy it to the intended register, (and restore the temporary register again if necessary)



The IN and OUT instructions can move data from one of the 32 registers to the I/O registers.

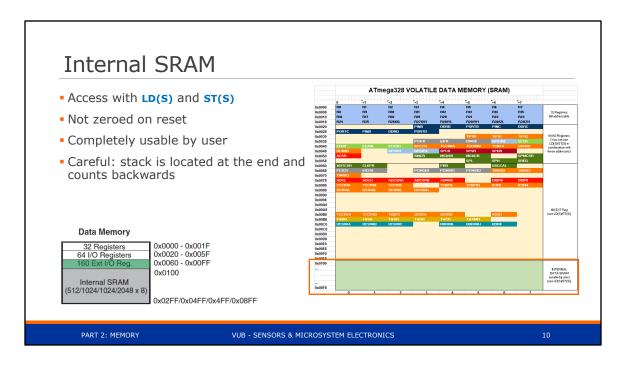
The include file (atmega328.inc) defines a number of identifiers for certain registers. For any register in the 64 I/O registers, these identifiers are only valid to be used with IN and OUT. These registers can be accessed using LDS and STS, but then the identifiers are not valid.



The 32 registers on which one can do operations.

64 I/O registers. And 160 extended I/O registers. These registers are used to configure the peripherals of the microcontroller.

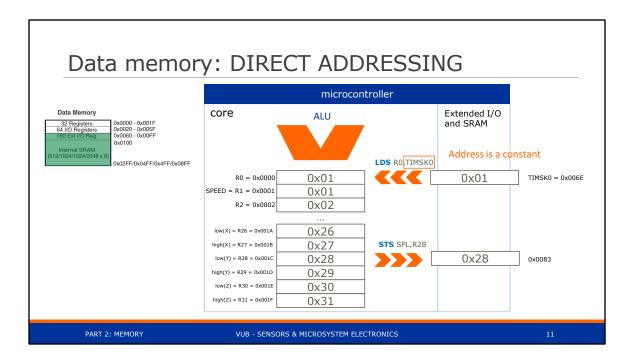
The internal SRAM: this is free memory space to be freely used by the programmer



The 32 registers on which one can do operations.

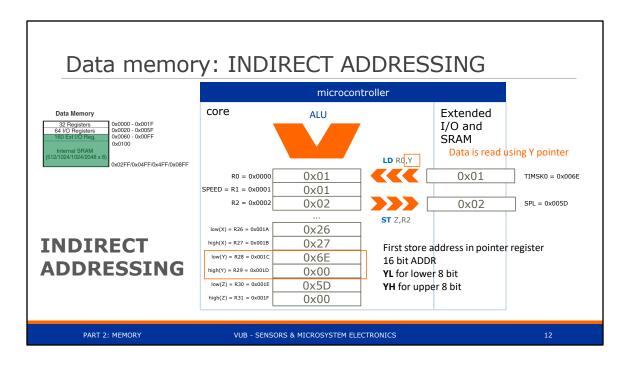
64 I/O registers. And 160 extended I/O registers. These registers are used to configure the peripherals of the microcontroller.

The internal SRAM: this is free memory space to be freely used by the programmer



For the remaining part of the memory, the LDS/LD and STS/ST instructions are used. Two different methods of memory access exist: Direct and indirect.

The direct method is done trough supplying the memory address to the LDS/STS instruction.



The other method is the indirect method. Here one first stores the 16-bit memory address in one of the three memory addressing registers of pointer register (each consisting of 2 separate registers to achieve 16bit addressing). After this, the memory address the register points to can be accessed using LD and ST

This method can be used to access consecutive memory locations or to calculate a certain memory address offset before using it to access that data.

Indirect addressing - Post-increment ;Code example: write 0xFF to First iteration (Y = 0x108): ;addresses 0x108 to 0x10E in SRAM ST writes R20 to 0x108 ∘ Y = Y + 1 after write ;Set Y pointer to 0x108 • 2nd iteration (Y = 0x109): LDI YH, high(0x0108); upper byte to YH (0x01) ST writes R20 to 0x109 LDI YL, low(0x0108); lower byte to YL (0x08) \circ Y = Y + 1 after write 3rd iteration (Y = 0x10A) LDI R20, 0xFF; some data in a register LDI R16, 8; loop iterator Loop: 8th iteration (Y = 0x10E) ST Y+, R20; store R20 in the current ST writes R20 to 0x109 address ∘ Y = Y + 1 after write DEC R16; decrement loop iterator BRNE Loop; end of loop Memory 4 • End of loop (Y = 0x110)→ Address: 0x0100,data 00 00 00 00 00 00 00 00 lata 0x0118 00 00 00 00 00 00 00 00 PART 2: MEMORY **VUB - SENSORS & MICROSYSTEM ELECTRONICS**

Here we have a look to the POST-Increment feature of the indirect addressing method. This is useful when reading or writing data from or to consecutive addresses.

First the Y pointer upper and lower byte is loaded with the right part of the address with the help of the HIGH and LOW directive. Next the value 0xFF is stored in R20 and a loop of 8 iterations with R16 as iterator is made.

By adding a plus after the Y pointer in the ST instruction line. The compiler knows to use the ST with Y and post-increment bytecode when compiling.

The first iteration will write the value from R20 to the address Y is pointing to, in this iteration this is still address 0x108 which is the first address of the user SRAM. After the write, Y will be incremented by one, now pointing to 0x109 (YH = 0x01 and YL = 0x09)

The second iteration will write the value from R20 to the address Y is currently pointing to, in this iteration this has become address 0x10A. After the write, Y will be incremented by one, now pointing to 0x10A (YH = 0x01 and YL = 0x0A)

After the eight iteration, the SRAM addresses 0x108 to 0x10E will contain 0xFF as value. Y will now point to 0x110 (YH = 0x01 and YL = 0x10). The figure shows a screenshot of the SRAM from the simulator displaying that the writing was successful.

Note that when any lower pointer register overflows due to the increment, the carry will be added into the upper pointer register. This post-increment is supported by both the ST and LD instruction. The PRE-increment option does not exist in this instruction set.

Indirect addressing – Pre-decrement ;Code example: write 0xFF to First iteration (Y = 0x108): ;addresses 0x108 to 0x100 in SRAM • Y = Y - 1 before write ST writes R20 to 0x107 ;Set Y pointer to 0x108 • 2nd iteration (Y = 0x107): LDI YH, high(0x0108);upper byte to YH (0x01) • Y = Y - 1 before write LDI YL, low(0x0108); lower byte to YL (0x08) o ST writes R20 to 0x106 3rd iteration (Y = 0x106) LDI R20, 0xFF ;some data in a register LDI R16, 8; loop iterator Loop: • 8th iteration (Y = 0x101)ST -Y, R20; store R20 in the current • Y = Y - 1 before write address ST writes R20 to 0x100 DEC R16; decrement loop iterator BRNE Loop; end of loop • End of loop (Y = 0x100)Memory: data IRAM Address: 0x0100.data data 0x0100 ff ff ff ff ff ff ff yyyyyyy data 0x0108 00 00 00 00 00 00 00 00 data 0x0110 00 00 00 00 00 00 00 00 00 data 0x0118 00 00 00 00 00 00 00 00 00 PART 2: MEMORY **VUB - SENSORS & MICROSYSTEM ELECTRONICS**

Here we have a look to the PRE-decrement feature of the indirect addressing method. This is useful when reading or writing data from or to consecutive addresses.

First the Y pointer upper and lower byte is loaded with the right part of the address with the help of the HIGH and LOW directive. Next the value 0xFF is stored in R20 and a loop of 8 iterations with R16 as iterator is made.

By adding a minus after the Y pointer in the ST instruction line. The compiler knows to use the ST with Y and pre-decrement bytecode when compiling.

In the first iteration will first decrement Y and then write the value from R20 to the address Y is pointing to. Before the decrement Y points to 0x108. This gets decremented to 0x107 and then the write is done to that address. After the write, Y will pointing to 0x107 (YH = 0x01 and YL = 0x07)

The second iteration will decrement Y from 0x107 to 0x106 before writing the value from R20 to the address Y is currently pointing to, in this iteration this has become address 0x106. After the write, Y will pointing to 0x106 (YH = 0x01 and YL = 0x06)

After the eight iteration, the SRAM addresses 0x107 to 0x100 will contain 0xFF as value. Y will now point to 0x100 (YH = 0x01 and YL = 0x00). The figure shows a screenshot of the SRAM from the simulator displaying that the writing was successful.

Note that when any lower register underflows due to the decrement, this carries over in the upper register. For example predecrement from 0x100 (YH = 0x01 and YL = 0x00) results in Y= 0x0FF (YH = 0x00 and YL = 0xFF). The post-decrement option does not exist in this instruction set.

Keywords & addresses

- R0 R31 are built into the compiler
- Non memory mapped (IO registers):
 - Use keyword with IN and OUT
 - Use exact address with IN and OUT
 - compensate 0x20 offset (IN Rx, [keyword] 0x20)
 - Can be used with LDS and STS (slower)
 - Keyword + 0x20
 - Exact address from memory overview excel
- Memory mapped (ext IO registers) :
 - Does NOT work with IN and OUT
 - Can be used with LDS and STS (slower)
 - Keyword
 - Exact address

m328pdef.inc

```
.equ TIMSK2= 0x70; MEMORY MAPPED
.equ TIMSK1= 0x6f; MEMORY MAPPED
.equ TIMSK0= 0x6f; MEMORY MAPPED
.equ PCMSK1= 0x6c; MEMORY MAPPED
.equ PCMSK2= 0x6c; MEMORY MAPPED
.equ PCMSK2= 0x69; MEMORY MAPPED
.equ PCICR= 0x66; MEMORY MAPPED
.equ OSCCAL= 0x66; MEMORY MAPPED
.equ OSCCAL= 0x66; MEMORY MAPPED
.equ OSCCAL= 0x66; MEMORY MAPPED
.equ CLKPR= 0x61; MEMORY MAPPED
.equ CLKPR= 0x61; MEMORY MAPPED
.equ SPL= 0x3d
.equ SPL= 0x3d
.equ SPL= 0x3d
.equ SPCS= 0x37
.equ MCUSR= 0x35
.equ MCUSR= 0x35
.equ MCUSR= 0x34
.equ SPCS= 0x26
.equ GPTOR1= 0x2a
.equ GPTOR1= 0x2a
.equ OCR0B= 0x28
```

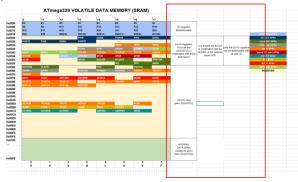
PART 2: MEMORY

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Memory overview

- See Section 8. AVR Memories in
- AT328P_microcontroller.pdf
- MemoryOverview.xlsx



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